

# Noise-induced backscattering in a quantum-spin-Hall edge

Jukka I. Väyrynen,<sup>1</sup> Dmitry I. Pikulin,<sup>1</sup> and Jason Alicea<sup>2,3</sup>

<sup>1</sup>Station Q, Microsoft Research, Santa Barbara, California 93106-6105, USA

<sup>2</sup>Department of Physics and Institute for Quantum Information and Matter,  
California Institute of Technology, Pasadena, CA 91125, USA

<sup>3</sup>Walter Burke Institute for Theoretical Physics, California Institute of Technology, Pasadena, CA 91125, USA  
(Dated: May 14, 2022)

Time-reversal symmetry suppresses electron backscattering in a quantum-spin-Hall edge, yielding quantized conductance at zero temperature. Understanding the dominant corrections in finite-temperature experiments remains an unsettled issue. We study a novel mechanism for conductance suppression: backscattering caused by incoherent electromagnetic noise. Specifically, we show that an electric potential fluctuating randomly in time can backscatter electrons inelastically without constraints faced by electron-electron interactions. We quantify noise-induced corrections to the dc conductance in various regimes and propose an experiment to test this scenario.

**Introduction.** From a technological perspective, the main promise of two-dimensional topological insulators (2D TIs) stems from their edge states, which are protected by a combination of symmetry and topology [1–3]. The ‘helical’ low-energy edge spectrum consists of *degenerate* counterpropagating electron states with opposite spins as required by time-reversal symmetry. Kramers orthogonality of the two states prevents elastic backscattering by a static potential, in turn yielding a quantized zero-temperature conductance  $G = G_0 \equiv e^2/h$  per edge. Perfect quantization has, however, so far eluded experimental observation [4–11].

In practice, it was realized early on that many *inelastic* effects circumvent band-topology constraints and can hinder the edge-mode propagation by introducing backscattering [12–22]. These backscattering mechanisms reflect the fact that time-reversal symmetry allows *non-degenerate* counterpropagating states to have overlapping spin wave functions. Such non-zero overlap occurs generically in systems with fully broken spin-rotation symmetry. Indeed, it is well known that structural or bulk inversion asymmetry in 2D TIs may induce nontrivial edge spin texture in momentum space [17]; that is, the edge-state spin quantization axis “rotates” as a function of momentum [23] as sketched in Fig. 1a. The necessary energy transfer for backscattering was considered to originate from thermal itinerant edge electrons or phonons, or fluctuating localized spins. Apart from the latter, the backscattering rate was found to be strongly suppressed at low temperatures: Electron-electron interactions perturbatively produce a conductance correction  $\delta G \equiv G_0 - G \propto T^4$  at low temperatures, while phonon scattering is even more suppressed. Localized spins impart a stronger effect in the perturbative limit,  $\delta G \propto \ln^2 T$ , but their presence in 2D TIs has not been experimentally verified and need not be a universal feature of all 2D TI materials.

In this paper we show that a time-dependent scalar potential might dominate the backscattering in practice. This mechanism is expected to be ever-present in all ma-

terials in the form of electrical noise and it is almost free from phase space constraints.

We start from a qualitative derivation of our main result, the estimate of the decrease  $\delta G$  in the edge dc conductance. The spin texture in momentum space leads to an off-diagonal component for the edge electron density operator expressed in terms of left and right movers [24]. In the long wave length limit it reads  $\rho_{\text{off-diag}}(x) \sim i \frac{v}{D} [\partial_x \psi_R^\dagger(x) \psi_L(x) - \psi_R^\dagger(x) \partial_x \psi_L(x)] + h.c.$ , where  $D/v$  is the momentum scale over which the spin rotates, see Fig. 1a. (We work in units where  $\hbar = k_B = 1$ .) The total density coupled to a scalar potential  $U(x)$  thus gives rise to an effective backscattering matrix element  $V_{pR \rightarrow p'L}$  which vanishes for small energy transfer  $v|p' + p|$  as  $V_{pR \rightarrow p'L} = v(p + p')D^{-1}U_{2k_F}$ . (Here  $v$  is the edge state Dirac velocity and  $p, p'$  are the momenta measured from the Fermi points  $\pm k_F$ ;  $U_{2k_F}$  is the  $2k_F$  Fourier component of the potential.) For a potential  $U$  fluctuating harmonically with frequency  $\omega$ , the backscattering rate is  $\Gamma = 2\pi\nu \frac{\omega^2}{D^2} |U_{2k_F}|^2$ , where  $\nu = 1/2\pi v$  is the edge density of states per length. When a bias voltage  $V$  is applied across the edge, there are  $\nu eV$  states that contribute to the current. Thus, we find the backscattered current at low-temperature,  $\delta I_\omega = e \Gamma \nu eV = 2\pi e^2 \nu^2 \frac{\omega^2}{D^2} |U_{2k_F}|^2 V$ . One needs to integrate  $\delta I_\omega$  over the full noise spectrum. For a noise caused by a single fluctuating dipole, modeled as a two-level system with relaxation rate  $\tau^{-1}$ , the integral over  $\omega$  is dominated by  $\omega \sim \tau^{-1}$ . This yields

$$\delta G = \frac{d\delta I_{1/\tau}}{dV} \sim G_0 \frac{1}{(D\tau v)^2} |U_{2k_F}|^2, \quad (1)$$

which is one of our main results. The refined version of this equation is given in Eq. (12). On a long edge, many dipoles contribute incoherently to  $\delta G$ , leading to resistive edge transport. The long edge resistance is obtained by summing Eq. (1) over impurities and by averaging over  $\tau$ . Assuming a distribution of relaxation times  $P(\tau) \sim 1/\tau$  and a short-time cutoff  $\tau_0$ , the resistance of an edge of

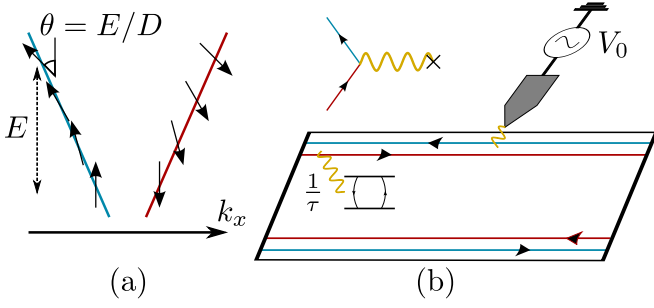


Figure 1. (a) Spin texture in momentum space. Over a small energy-interval  $E$ , the spin of an eigenstate rotates by a small angle  $E/D$ . (b) A time-dependent scalar potential leads to backscattering when spin-rotation symmetry is broken. The time-dependent potential may occur due to a fluctuating two-level system near the edge or from an external gate, see respective Eqs. (12), (15) for the resulting decrease in dc conductance. The latter mechanism allows for a simple way to probe the breaking of spin rotation symmetry. A nearby gate is used to modulate the electric potential at the edge locally. When an ac voltage  $V_0 \cos \omega_0 t$  is applied to the gate, the measured two-terminal dc conductance will decrease according to Eq. (15).

length  $L$  becomes

$$R \sim LnG_0^{-1} \frac{1}{(D\tau_0 v)^2} |U_{2k_F}|^2, \quad (2)$$

where  $n$  is the number of dipoles per length. Given that fluctuating dipoles can be used to model  $1/f$  noise [25], it is not surprising that Eq. (2) gives also the resistance caused by a  $1/f^\alpha$  noise spectrum with high-frequency cutoff  $\tau_0^{-1} < D$  and  $0 < \alpha < 3$ . Equations (1)–(2) are valid at high temperatures when the dipoles are not frozen. In this range the mechanism does not lead to strong temperature-dependence of  $R$ , unlike the conventional backscattering ones.

Based on this result we make a prediction that backscattering can be generated by applying ac voltage to a gate near the edge, see Fig. 1b. Using the above intermediate formula for  $\delta I_\omega$ , we see that indeed a monochromatic potential  $\sim U \cos \omega t$  applied to a nearby gate decreases the edge dc conductance by  $\delta G \sim \omega^2 D^{-2} |U|^2$ , see Eq. (15). The observation of such quadratic increase of  $\delta G$  with the gate voltage frequency and amplitude would provide strong evidence for the breaking of spin rotation symmetry in topological insulator edge.

**Model and derivation.** The Hamiltonian of a clean helical edge is [17]

$$H_0 = \int \frac{dk}{2\pi} (\varepsilon_k c_{kR}^\dagger c_{kR} + \varepsilon_{-k} c_{kL}^\dagger c_{kL}), \quad (3)$$

where we linearize the spectrum  $\varepsilon_k = vk - \mu$  around the chemical potential  $\mu = vk_F$ . The form of  $H_0$  does not assume spin conservation and allows for a spin texture

in momentum space. The spin of an eigenstate is found from the unitary transformation

$$\begin{pmatrix} c_{k\uparrow} \\ c_{k\downarrow} \end{pmatrix} = B_k \begin{pmatrix} c_{kR} \\ c_{kL} \end{pmatrix}, \quad (4)$$

that relates a chosen spin direction to left and right movers. Unitarity and time-reversal symmetry impose  $B_k^\dagger = B_k^{-1}$  and  $B_k = B_{-k}$ , respectively [26].

Consider next a time-dependent scalar potential that couples to the density of the edge electrons  $\rho = \sum_{\sigma=\uparrow,\downarrow} \psi_\sigma^\dagger \psi_\sigma$ :

$$H_U(t) = \int dx \rho(x) U(x) w(t). \quad (5)$$

We assume here that the noise-induced potential has a separable dependence on position and time, parametrized by  $U$  and  $w$ , respectively. This assumption is certainly true for telegraph noise (two-level system noise) from a single impurity, which we consider later.

Using Eq. (4) to write the density operator  $\rho$  in the  $L/R$ -basis, we see that  $H_U$  does not conserve the number of left and right movers. In momentum representation, the off-diagonal part of Eq. (5) is

$$H_{U,RL}(t) = w(t) \int \frac{dk}{2\pi} \frac{dk'}{2\pi} [B_{k'}^\dagger B_k]_{10} U_{k-k'} c_{k'R}^\dagger c_{kL} + h.c.. \quad (6)$$

Equation (6) gives rise to a non-zero backscattering current operator  $\delta I(t) = -\frac{1}{2} e d (N_R - N_L) / dt$ .

We evaluate the average backscattering current  $\langle \delta I(t) \rangle$  by employing the Kubo formula, treating  $H_{U,RL}$  as a time-dependent perturbation. We find

$$\begin{aligned} \langle \delta I(t) \rangle &= e \int \frac{dk}{2\pi} \frac{dk'}{2\pi} |[B_{k'}^\dagger B_k]_{10}|^2 |U_{k-k'}|^2 (f_{-kL} - f_{kR}) \\ &\times 2\text{Re} \int_{-\infty}^0 dt' e^{-i(vk+vk'+i0)t'} w(t) w(t'+t). \end{aligned} \quad (7)$$

As a sanity check, one can see that a static perturbation,  $w(t) = w$  does not lead to backscattering since it would impose  $k = -k'$  and thus  $[B_{k'}^\dagger B_k]_{10} = 0$  in Eq. (7). In Eq. (7) we introduced the Fermi functions  $f_{k\alpha} = f(\alpha vk - \mu_\alpha) = \langle c_{k\alpha}^\dagger c_{k\alpha} \rangle$  and  $f(E) = (e^{E/T} + 1)^{-1}$ . The bias voltage  $V$  is implemented by setting different chemical potentials  $\mu_{R,L} = \mu \pm \frac{1}{2} eV$  for left and right movers. We will next take the linear-response limit,  $eV \ll T$ ,  $f_{-kL} - f_{kR} \approx f(vk - \mu)[1 - f(vk - \mu)]eV/T$ .

The time-averaged backscattered current (*i.e.*, its dc component),  $\overline{\langle \delta I \rangle} = \mathcal{T}^{-1} \int_0^{\mathcal{T}} dt \langle \delta I(t) \rangle$  as  $\mathcal{T} \rightarrow \infty$ , is determined by the Fourier transform of the correlator  $\overline{w(t'+t)w(t)}$ . In terms of the power spectral density  $S(\omega) = \int_{-\infty}^{\infty} dt' e^{i\omega t'} \overline{w(t)w(t'+t)}$ , the time-averaged correction to conductance,  $\delta G = d\overline{\langle \delta I \rangle} / dV$ , can be written

as

$$\delta G = e^2 \int \frac{dk}{2\pi} \frac{dk'}{2\pi} |[B_{k'+k_F}^\dagger B_{k+k_F}]_{10}|^2 \quad (8)$$

$$\times |U_{k+k'+2k_F}|^2 T^{-1} f(vk)[1 - f(vk)] S(vk - vk').$$

The power spectral density is always positive, and therefore the noise always decreases the dc edge conductance,  $\delta G > 0$ . Note that, in general  $\overline{w(t)} \neq 0$  and there is a disconnected contribution to the average  $\overline{w(t'+t)w(t)}$ . However, that piece gives rise to a static term  $\propto \delta(\omega)$  to  $S(\omega)$  and thus does not contribute to  $\overline{\langle \delta I \rangle}$ .

**Telegraph noise from a charge puddle.** The correction to conductance  $\delta G$ , Eq. (8), depends on the noise spectrum. A realistic source is telegraph noise caused by a charge puddle [19] with a fluctuating charge. We can model the puddle as a quantum dot with different charge states. Depending on its charge state at a given time  $t$ , the dot creates a local electric potential  $W(x, t)$  on the edge. If the dot has a sizable charging energy  $E_C \gtrsim T$ , it is sufficient to only include two charge states in our description. In this case, the puddle acts as a two-level system (TLS) akin to a fluctuating dipole and its potential has the separable form  $U(x)w(t)$  in Eq. (5). Here  $U(x)$  is the effective dipole potential (the difference in the potential in the two charge states) and  $w(t)$  will be telegraph noise. We assume that the largest dipole potential is given by different charge states; to simplify our description, we therefore ignore different states of the puddle in the same charge sector. (Note also that the monopole potential,  $\overline{W}(x, t)$ , does not fluctuate and therefore has no effect on backscattering.) The noise spectrum is given by [25]

$$S(\omega) = p_0(1 - p_0) \frac{2\tau}{1 + \omega^2\tau^2}, \quad (9)$$

where  $\tau^{-1}$  is the relaxation rate of the excited state and  $p_0$  is the probability for the TLS to be in its ground state. For a thermal population,  $p_0 = 1/(1 + e^{-\Delta/T})$ , where  $\Delta$  is the energy-difference between excited and ground states. For a charge puddle, we have  $\Delta = 2E_C|\{N_g\} - \frac{1}{2}|$  where  $\{\dots\}$  denotes the positive fractional part and  $N_g$  is a dimensionless parameter determined by the puddle's electrostatic environment (*e.g.*, a neighboring puddle) and thus varies between different TLSs. We treat  $N_g$  as a random variable with a uniform distribution. We note however that  $N_g$  has a linear dependence on the edge chemical potential  $\mu$  which is tunable by a global gate. Therefore, due to the factor  $p_0(1 - p_0)$  in Eq. (9), we expect to see temperature-broadened resonances in  $\delta G$  of a short edge as gate voltage is tuned, see Eq. (12) below. Fluctuations of conductance as a function of gate voltage is consistent with experiments in the present 2D TI candidate materials [4, 10, 27].

The integrals in Eq. (8) cannot be explicitly carried out without specifying the functional form  $B_k$  of the spin

texture. However, when  $B_k$  is a slowly-varying function over the energy scales relevant to our problem, we can do an approximation. In the integrand in Eq. (8) the function  $S(vk - vk')$ , Eq. (9), confines  $vk'$  to within  $\tau^{-1}$  of  $vk$ . Assuming  $\tau^{-1} \ll D$ , we can approximate

$$B_{k+k_F+i\tau^{-1}/v} \approx B_{k+k_F} + \frac{i}{D\tau} B_{k+k_F}^{(1)}, \quad (10)$$

where  $B^{(1)} = dB/dk$ . Neglecting the effect of  $\tau^{-1}$  on  $U$ , we can do the integral over  $k'$ , by using Eq. (10), to get

$$\delta G = 2\pi e^2 \frac{\nu T^{-1}}{(D\tau)^2} p_0(1 - p_0) \int \frac{dk}{2\pi} |U_{2k+2k_F}|^2 \quad (11)$$

$$\times |[B_{k+k_F}^{(1)\dagger} B_{k+k_F}]_{10}|^2 f(vk)[1 - f(vk)].$$

The Fermi functions confine  $E$  to be of the order of  $T$ . When also  $T \ll D$ ,  $\mu$ , we further find

$$\delta G = G_0 \frac{1}{(D\tau\nu)^2} |U_{2k_F}|^2 p_0(1 - p_0) |[B_{k_F}^{(1)\dagger} B_{k_F}]_{10}|^2. \quad (12)$$

This is the more refined version of Eq. (1) derived in the introduction from elementary arguments. Note that Eq. (12) is valid for any  $\mu/D$ . However, in the limit  $\mu/D \ll 1$ , the first derivative becomes small,  $B_{k_F}^{(1)\dagger} \approx \frac{\mu}{D} B_{k=0}^{(2)}$ , because of the property  $B_k = B_{-k}$ . Even though we derived Eq. (12) in the limit  $eV \ll T$ , the result is valid for any  $eV/T$  as long as  $\max(eV, T) \ll \mu, D$ .

Finally, let us comment on the fluctuations of the backscattering current, defined as  $\mathcal{S}_{\delta I}(\omega) = \int_{-\infty}^{\infty} dt' e^{i\omega t'} \text{Re}\langle \delta I(t) : \delta I(t+t') : \rangle$  where  $: \delta I : \equiv \delta I - \langle \delta I \rangle$ . For generic  $\tau^{-1}$  and  $\omega$  there is no simple relation between  $\mathcal{S}_{\delta I}$  and  $\overline{\langle \delta I \rangle}$ . However, in the limit  $\omega, T, eV \ll D, \mu$  and  $\tau^{-1} \ll T$ , we find the standard results of weak backscattering of non-interacting electrons:  $\mathcal{S}_{\delta I}(0) = e\overline{\langle \delta I \rangle}$  in the shot noise limit  $eV \gg T$  and  $\mathcal{S}_{\delta I}(\omega) = \delta G \omega \coth \frac{\omega}{2T}$  in the equilibrium limit  $V = 0$ .

**Long edge.** Equation (12) derived above is valid for a single fluctuating TLS which is the relevant case for a short edge. Next, we shall consider the effects of multiple TLSs near the edge, which is appropriate for a long edge. The correction to conductance, Eq. (12), due to a single TLS can be translated into an added small resistance  $\delta R = \delta G/G_0^2 \ll G_0^{-1}$  to the total edge resistance,  $R \approx G_0^{-1} + \delta R$ . Assuming the fluctuations of the TLSs are uncorrelated, we can neglect interference contributions [28] and the resistance of a long edge is given by  $R \approx \sum_i \delta R_i$  where  $\delta R_i$  is the contribution from the  $i$ th TLS. Summing over  $i$  amounts to ensemble-averaging Eq. (12) over the random parameters, in particular  $N_g$ . The average is dominated by those puddles where  $N_g$  is close to a half-integer,  $\Delta \ll T$ . Interpreting  $\tau^{-1}$  and  $|U_{2k_F}|^2$  as their typical values at  $\{N_g\} \approx 1/2$ , we find therefore an edge resistance

$$R = LnG_0^{-1} \frac{1}{2(D\tau\nu)^2} |U_{2k_F}|^2 |[B_{k_F}^{(1)\dagger} B_{k_F}]_{10}|^2 \frac{T}{E_C} \tanh \frac{E_C}{2T}, \quad (13)$$

where  $n$  is the one-dimensional impurity density [29] and  $L$  is the length of the edge. The factor  $(2T/E_C) \tanh \frac{E_c}{2T} = 4\langle p_0(1-p_0) \rangle_{N_g}$  is the fraction of TLS for which  $T \gg \Delta$ . The noise time scale  $\tau$  can be estimated by evaluating the escape rate of an electron from one charge puddle to a neighboring puddle. Since  $\{N_g\} \approx 1/2$ , tunneling is resonant and its rate is equal to the level splitting in the two-puddle problem. We can use the WKB approximation since the puddles are typically large [21]. This estimate gives  $\tau^{-1} \sim \delta e^{-d/\Lambda}$ , where  $\delta$  is the puddle level spacing,  $\Lambda$  is the penetration depth of a low-energy electron into the bulk and  $d$  is the average distance between the puddles. In the limit  $T \gg E_c$  the resistance, Eq. (13) is independent of temperature, while at low temperatures  $R \propto T$ . Strictly speaking, at  $T \gg E_c$  one should include more charge states in our noise model. As long as  $\tau^{-1} \ll E_c$ , the puddle charge takes discrete well-defined values and the noise has the Lorentzian form, Eq. (9), dominated by  $\omega \sim \tau^{-1}$ , independent of temperature. The generalization of the prefactor  $p_0(1-p_0)$  in that equation to many levels remains  $T$ -independent at high temperatures. While many levels offers a quadratic increase in the number of possible charge transitions, the corresponding probability of transition decreases similarly quadratically in the number of levels.

**1/f noise.** In Eq. (13) we took  $\tau^{-1} \sim \delta e^{-d/\Lambda}$  with  $d$  the puddle-puddle distance. Assuming that the random variable  $d$  is distributed uniformly, the corresponding distribution of relaxation times,  $P(\tau) \sim 1/\tau$ , is dominated by short times  $\tau \sim 1/\delta$ . The resistance averaged over puddle positions becomes then

$$R \sim LnG_0^{-1} \frac{\delta^2}{D^2 v^2} |U_{2k_F}|^2 |[B_{k_F}^{(1)\dagger} B_{k_F}]_{10}|^2, \quad (14)$$

in the high-temperature limit. This same result is obtained when the electrical noise has a  $1/f$  spectrum with an upper cutoff  $\delta$ , as can be seen by averaging Eq. (9) over  $\tau$  with the distribution  $1/\tau$ . To model more generic  $1/f^\alpha$  noise, we take a spectrum  $S(\omega) = |\omega|^{-\alpha} D_1^{\alpha-1} S_0$ , defined for  $D_0 < |\omega| < D_1$ . Here  $\alpha > 0$  and  $S_0$  is a dimensionless constant. Using Eq. (8) and the approximations leading to Eq. (12), the resulting resistance has the same form as Eq. (14) with replacement  $\delta \rightarrow D_1$ , up to numerical factors. We have assumed  $\alpha < 3$  in which case one can take the limit  $D_0 \rightarrow 0$ .

**Experimental implementation.** The noise-induced backscattering, Eq. (8), relies on the presence of a momentum-space spin texture of the edge state. Although band theory predicts the existence of such a texture [30], its experimental detection is so far absent. In this section, we propose a simple experiment that allows one to probe the spin rotation in momentum space.

We suggest to create a time-dependent “noise potential” artificially by an external gate, see Fig. 1b. With ac voltage  $V_0 \cos \omega_0 t$  applied to the gate, we can set the gate-

induced electric potential on the edge,  $U(x) = V_0 u(x)$ , and time-dependence  $w(t) = \cos \omega_0 t$  in Eq. (5). The dimensionless function  $u(x)$  is geometry-dependent and can be in principle found by solving the Poisson equation.

Using Eq. (8) with  $S(\omega)$  obtained from  $w$ , we find in the limit  $\omega_0, T \ll D, \mu$ ,

$$\delta G = G_0 \frac{\omega_0^2}{2D^2 v^2} V_0^2 |u_{2k_F}|^2 |[B_{k_F}^{(1)\dagger} B_{k_F}]_{10}|^2. \quad (15)$$

Remarkably, by the application of an ac gate voltage, one may create an effective backscattering potential  $\propto \omega_0 V_0 u_{2k_F} [B_{k_F}^{(1)\dagger} B_{k_F}]_{10}/D$  on the helical edge, as long as a spin texture exists. Quadratic dependence of  $\delta G$  on gate voltage and frequency would thus be a clear experimental signature of a spin texture in a helical edge. Let us note that for large  $k_F = \mu/v$  it may be difficult in practice to create a sharp enough potential that has large  $u_{2k_F}$ . This difficulty can be avoided if the Dirac point is not buried [11, 31] and one can tune  $k_F$  with a global gate to a smaller value. In this limit there is an additional  $\mu$ -dependence in  $\delta G$  stemming from  $B_{k_F}^{(1)\dagger} \approx \frac{\mu}{D} B_{k=0}^{(2)}$ .

**Discussion.** Let us finally give estimates for the parameters of the charge puddle model and discuss the applicability of our results. Using the estimates for HgTe [32] and  $\tau^{-1} \sim \delta e^{-1/n_p^{1/2} \Lambda}$ ,  $\Lambda \approx v/\Delta_b$ , we find  $\tau^{-1} \sim 10^{-3} \Delta_b$  where  $\Delta_b$  is the band gap. As was mentioned in the context of Eq. (14), the dominant contribution to resistance comes from close pairs of puddles for which  $\tau^{-1} \approx \delta \approx 0.1 \Delta_b$ . For a ball-park estimate of  $U_{2k_F}$ , we can use the charging energy  $E_c \sim \alpha v/l$  of a charge puddle of size  $l$ , denoting  $\alpha = e^2/\kappa v$ . Assuming a short-range potential then gives  $U_{2k_F} \sim v\alpha$ . Taking  $|[B_{k_F}^{(1)\dagger} B_{k_F}]_{10}| \sim 1$  by using  $v \sim 1/v$ , we obtain the final estimate for the resistance in Eq. (14),  $R \sim LnG_0^{-1} \alpha^4 \Delta_b^2 / D^2$ .

Our main results, Eqs. (12)–(13), and the above estimates were derived for a specific model of a fluctuating dipole in thermal equilibrium. We emphasize that these results generalize to the case of a non-equilibrium noise source. An important example is when effective noise temperature is much higher than the system temperature. The result for that case can be obtained by taking the high temperature limit  $p_0 \rightarrow 1/2$  and  $T \gg E_c$  in the respective equations Eqs. (12)–(13).

Finally, let us point out that there is also a magnetic field caused by the time-varying electric field (Maxwell’s correction to Ampere’s law). However, this field is tiny as it scales with the inverse speed of light squared. A field  $10^{-7}$  T would require an amplitude 1 eV of the potential when applied at frequency 10 GHz. Our mechanism has a different origin and will therefore generically give a much larger effect.

**Acknowledgments.** We gratefully acknowledge support from the National Science Foundation through grant DMR-1723367; the Caltech Institute for Quantum Information and Matter, an NSF Physics Frontiers Center

with support of the Gordon and Betty Moore Foundation through Grant GBMF1250; and the Walter Burke Institute for Theoretical Physics at Caltech.

- 
- [1] C. L. Kane and E. J. Mele, Physical Review Letters **95**, 146802 (2005), cond-mat/0506581.
- [2] C. L. Kane and E. J. Mele, Physical Review Letters **95**, 226801 (2005), cond-mat/0411737.
- [3] B. A. Bernevig and S.-C. Zhang, Physical Review Letters **96**, 106802 (2006), cond-mat/0504147.
- [4] M. König, S. Wiedmann, C. Brüne, A. Roth, H. Buhmann, L. W. Molenkamp, X.-L. Qi, and S.-C. Zhang, Science **318**, 766 (2007), arXiv:0710.0582.
- [5] A. Roth, C. Brüne, H. Buhmann, L. W. Molenkamp, J. Maciejko, X.-L. Qi, and S.-C. Zhang, Science **325**, 294 (2009), arXiv:0905.0365.
- [6] G. M. Gusev, Z. D. Kvon, E. B. Olshanetsky, A. D. Levin, Y. Krupko, J. C. Portal, N. N. Mikhailov, and S. A. Dvoretzky, Phys. Rev. B **89**, 125305 (2014).
- [7] I. Knez, C. T. Rettner, S.-H. Yang, S. S. P. Parkin, L. Du, R.-R. Du, and G. Sullivan, Phys. Rev. Lett. **112**, 026602 (2014).
- [8] L. Du, I. Knez, G. Sullivan, and R.-R. Du, Phys. Rev. Lett. **114**, 096802 (2015).
- [9] F. Nichele, H. J. Suominen, M. Kjaergaard, C. M. Marcus, E. Sajadi, J. A. Folk, F. Qu, A. J. A. Beukman, F. K. de Vries, J. van Veen, S. Nadj-Perge, L. P. Kouwenhoven, B.-M. Nguyen, A. A. Kiselev, W. Yi, M. Sokolich, M. J. Manfra, E. M. Spanton, and K. A. Moler, New Journal of Physics **18**, 083005 (2016).
- [10] Z. Fei, T. Palomaki, S. Wu, W. Zhao, X. Cai, B. Sun, P. Nguyen, J. Finney, X. Xu, and D. H. Cobden, Nature Physics **13**, 677 (2017), arXiv:1610.07924.
- [11] S. Wu, V. Fatemi, Q. D. Gibson, K. Watanabe, T. Taniguchi, R. J. Cava, and P. Jarillo-Herrero, Science **359**, 76 (2018), <http://science.sciencemag.org/content/359/6371/76.full.pdf>.
- [12] C. Xu and J. E. Moore, Phys. Rev. B **73**, 045322 (2006), cond-mat/0508291.
- [13] C. Wu, B. A. Bernevig, and S.-C. Zhang, Physical Review Letters **96**, 106401 (2006), cond-mat/0508273.
- [14] J. Maciejko, C. Liu, Y. Oreg, X.-L. Qi, C. Wu, and S.-C. Zhang, Physical Review Letters **102**, 256803 (2009), arXiv:0901.1685.
- [15] Y. Tanaka, A. Furusaki, and K. A. Matveev, Physical Review Letters **106**, 236402 (2011), arXiv:1102.4629.
- [16] J. C. Budich, F. Dolcini, P. Recher, and B. Trauzettel, Physical Review Letters **108**, 086602 (2012), arXiv:1109.5188.
- [17] T. L. Schmidt, S. Rachel, F. von Oppen, and L. I. Glazman, Phys. Rev. Lett. **108**, 156402 (2012).
- [18] V. Cheianov and L. I. Glazman, Physical Review Letters **110**, 206803 (2013), arXiv:1301.1185.
- [19] J. I. Väyrynen, M. Goldstein, and L. I. Glazman, Physical Review Letters **110**, 216402 (2013), arXiv:1303.1766.
- [20] B. L. Altshuler, I. L. Aleiner, and V. I. Yudson, Physical Review Letters **111**, 086401 (2013), arXiv:1306.2626.
- [21] J. I. Väyrynen, M. Goldstein, Y. Gefen, and L. I. Glazman, Phys. Rev. B **90**, 115309 (2014), arXiv:1406.6052.
- [22] N. Kainaris, I. V. Gornyi, S. T. Carr, and A. D. Mirlin, Phys. Rev. B **90**, 075118 (2014), arXiv:1404.3129.
- [23] The spin quantization can also be broken in a disordered manner; in this paper we ignore these terms for simplicity. Note that they do not lead to significant backscattering at low temperature [24].
- [24] H.-Y. Xie, H. Li, Y.-Z. Chou, and M. S. Foster, Phys. Rev. Lett. **116**, 086603 (2016).
- [25] S. Kogan, *Electronic Noise and Fluctuations in Solids* (Cambridge University Press, 1996).
- [26] As a  $2 \times 2$  unitary matrix,  $B_k$  can be written in terms of the Pauli matrices as  $B_k = \exp i\mathbf{d}_k \cdot \boldsymbol{\sigma}$  where  $\mathbf{d}_k$  is real. Time-reversal symmetry imposes  $\sigma^y B_k^* \sigma^y = B_{-k}$  which leads to  $\mathbf{d}_k = \mathbf{d}_{-k}$  and the condition given in the text.
- [27] T. Li, P. Wang, H. Fu, L. Du, K. A. Schreiber, X. Mu, X. Liu, G. Sullivan, G. A. Csáthy, X. Lin, and R.-R. Du, Phys. Rev. Lett. **115**, 136804 (2015).
- [28] For example, in the case of two TLSs, of the form Eq. (6), the interference term will be proportional to  $w_1(t)w_2(t+t')$ , whose average over  $t$  is independent of  $t'$  and therefore it doesn't contribute to  $\overline{\langle \delta I \rangle}$  for the same reason as a static perturbation does not contribute to it.
- [29] The density  $n$  is obtained from the two-dimensional density  $n_{2D}$  by multiplying the latter with the effective range  $\xi$  of the potential  $U$ ;  $n = n_{2D} \xi$ . In practice,  $\xi$  is the screening length given by the distance to nearest gate.
- [30] A. Rod, T. L. Schmidt, and S. Rachel, Phys. Rev. B **91**, 245112 (2015).
- [31] R. Skolasinski, D. I. Pikulin, J. Alicea, and M. Wimmer, ArXiv e-prints (2017), arXiv:1709.04830.
- [32] From Ref. [21] we have  $\delta \approx \alpha^2 \Delta_b$ ,  $\Lambda \approx 36 \text{ nm}$ ,  $n_p^{-1/2} \approx 174 \text{ nm}$ , and  $\alpha \approx 0.3$ .